XP133A1145SR

TOREX

Power MOS FET

- ◆N-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance: 0.045Ω (max)
- ◆Ultra High-Speed Switching
- ◆SOP-8 Package
- ◆Two FET Devices Built-in

■Applications

- ●Notebook PCs
- ●Cellular and portable phones
- ●On-board power supplies
- ●Li-ion battery systems

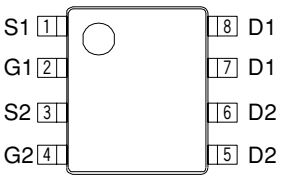
■General Description

The XP133A1145SR is an N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.
Two FET devices are built into the one package.
Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.
The small SOP-8 package makes high density mounting possible.

■Features

Low on-state resistance : Rds(on)=0.033Ω (Vgs=10V)
: Rds(on)=0.045Ω (Vgs=4.5V)
Ultra high-speed switching
Operational Voltage : 4.5V
High density mounting : SOP-8

■Pin Configuration

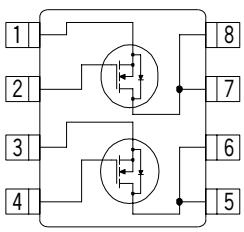


SOP-8
(TOP VIEW)

■Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5~6	D2	Drain
7~8	D1	Drain

■Equivalent Circuit



N-Channel MOS FET
(2 devices built-in)

■Absolute Maximum Ratings

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	30	V
Gate-Source Voltage	Vgss	±20	V
Drain Current (DC)	Id	6	A
Drain Current (Pulse)	Idp	20	A
Reverse Drain Current	Idr	6	A
Continuous Channel Power Dissipation (note)	Pd	2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55~150	°C

Note: When implemented on a glass epoxy PCB

■Electrical Characteristics

DC Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds=30V, Vgs=0V			10	μA
Gate-Source Leakage Current	Igss	Vgs=±20V, Vds=0V			±1	μA
Gate-Source Cut-off Voltage	Vgs(off)	Id=1mA, Vds=10V	1.0		2.5	V
Drain-Source On-state Resistance (note)	Rds(on)	Id=3A, Vgs=10V		0.026	0.033	Ω
		Id=3A, Vgs=4.5V		0.035	0.045	Ω
Forward Transfer Admittance (note)	|Yfs|	Id=3A, Vds=10V		12		S
Body Drain Diode Forward Voltage	Vf	If=6A, Vgs=0V		0.85	1.1	V

Note: Effective during pulse test.

Dynamic Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz		620		pF
Output Capacitance	Coss			350		pF
Feedback Capacitance	Crss			120		pF

Switching Characteristics

Ta=25°C

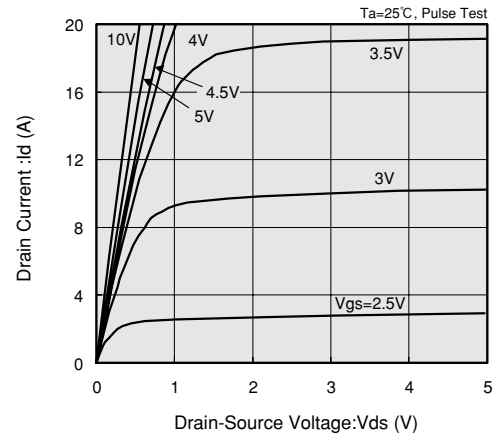
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs=5V, Id=3A Vdd=10V		15		ns
Rise Time	tr			20		ns
Turn-off Delay Time	td (off)			30		ns
Fall Time	tf			10		ns

Thermal Characteristics

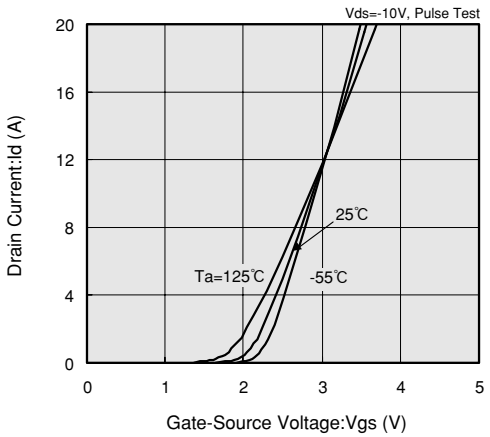
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB		62.5		°C/W

■Typical Performance Characteristics

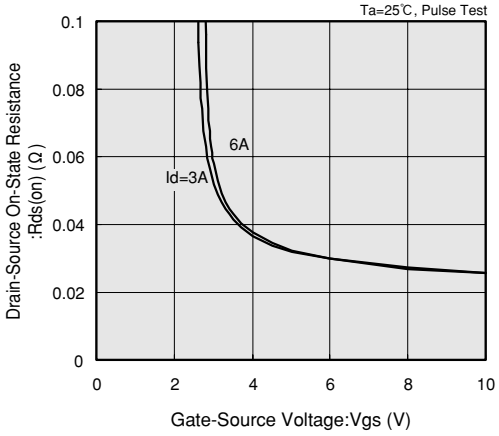
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



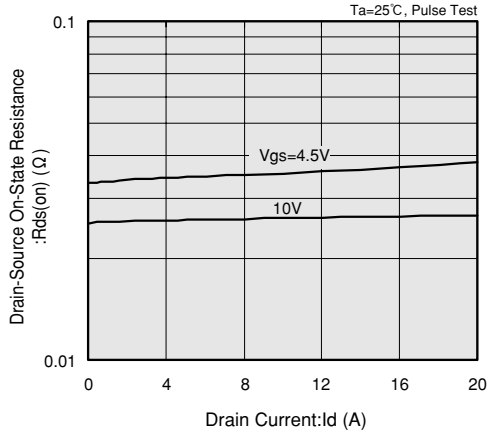
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



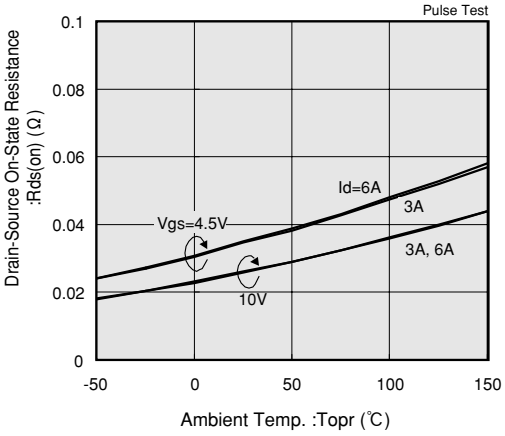
DRAIN-SOURCE ON-STATE RESISTANCE
vs. GATE-SOURCE VOLTAGE



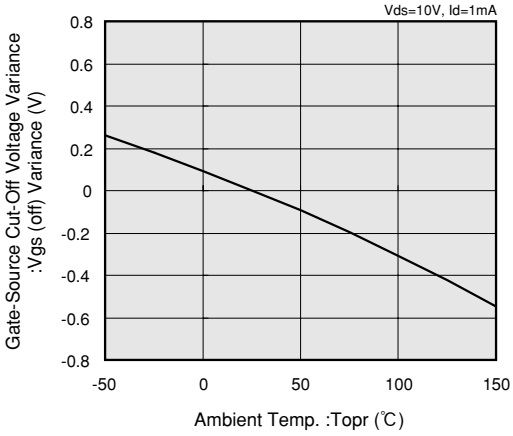
DRAIN-SOURCE ON-STATE RESISTANCE
vs. DRAIN CURRENT



DRAIN-SOURCE ON-STATE RESISTANCE
vs. AMBIENT TEMPERATURE



GATE-SOURCE CUT-OFF VOLTAGE VARIANCE
vs. AMBIENT TEMPERATURE



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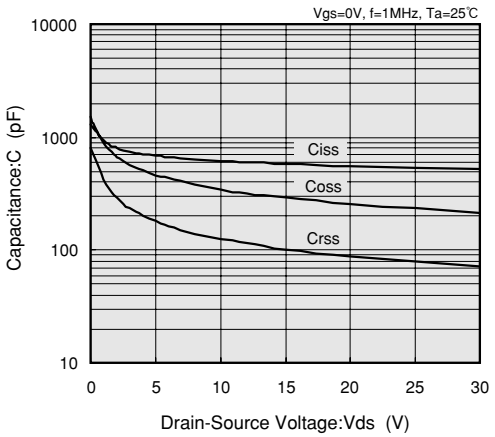
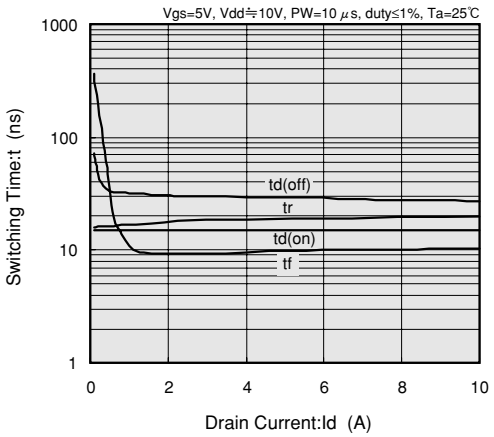
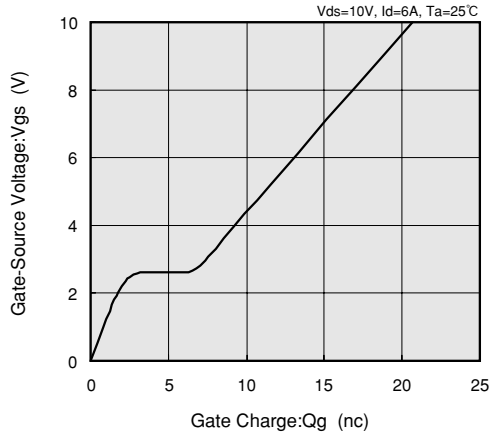
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



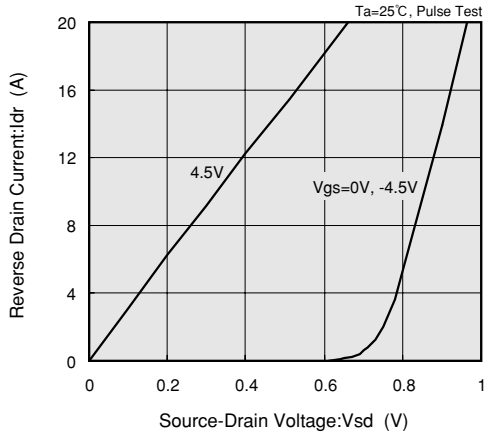
SWITCHING TIME vs. DRAIN CURRENT



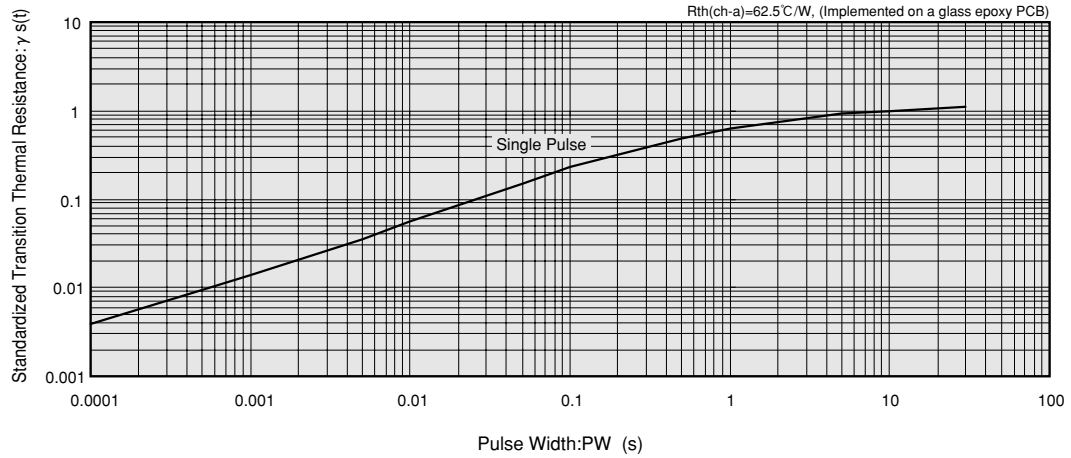
GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT
vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH



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